

Product Overview

MBRA1H100: Schottky Power Rectifier, Surface Mount, 1.0 A, 100 V

For complete documentation, see the data sheet.

The Schottky Rectifier employs the Schottky Barrier principle in a metal-to-silicon power rectifier. It features epitaxial construction with oxide passivation and metal overlay contact. It is ideally suited for low voltage, high frequency switching power supplies, free wheeling diodes and polarity protection diodes.

Features

- Low Forward Voltage Drop
- Small Compact Surface Mountable Package with J-Bent Leads
- Rectangular Package for Automated Handling
- Highly Stable Oxide Passivated Junction
- Guardring for Stress Protection
- This is a Pb-Free Device Mechanical Characteristics:
- Case: Epoxy, Molded
- Weight: 70 mg (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

For more features, see the data sheet

Benefits

- Low Power Loss/High Efficiency

Applications

- Low Voltage, High Frequency Rectification
- Free Wheeling Diodes
- Polarity Diodes

End Products

- Adapter

Part Electrical Specifications

Product	Compliance	Status	Configurati on	V_{RRM} Min (V)	V_F Max (V)	I_{RM} Max (μ A)	$I_{O(rec)}$ Max (A)	I_{FSM} Max (A)	t_r Max (ns)	C Max (pF)	Package Type
MBRA1H100T3G	Pb-free	Active	Single	100	0.76	40	1	50	-	-	SMA-2
	Halide free										
NRVBA1H100T3G	AEC Qualified PPAP Capable Pb-free Halide free	Active	Single	100	0.76	40	1	50	-	-	SMA-2

For more information please contact your local sales support at www.onsemi.com.

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